**In the Specification**

Please replace the paragraph beginning at page 11, line 11 to page 12, line 6 with the following replacement paragraph.

One consideration in selecting a material for the barrier layer is the thickness and density of the barrier layer that will be sufficient to achieve a desired level of oxygen diffusion reduction. Another factor to evaluate is that the barrier layer might be considered to form a part of a capacitor dielectric when the barrier layer contacts the dielectric layer since the barrier layer is insulative. Accordingly, it may be advantageous to recalculate the desired dimensions of a dielectric layer contacted by the barrier layer accounting for the presence of the additional insulative material. Accordingly, an "insulative" material as the term is used herein designates a material exhibiting a conductivity at 20°C of less than [[$10^{4}$]] $\underline{10^{-12}}$ microOhm$^{-1}$ centimeter$^{-1}$. As an alternative, an "insulative" material in the present context might be viewed as a material that impacts the capacitance otherwise achieved without the material. Generally, a "conductive" or "semiconductive" material might not produce a change in capacitance as such a barrier layer. A combined capacitor dielectric and insulative barrier layer according to the aspects of the invention can exhibit a leakage current of less than about $10^{-15}$ amps per cell and yield a capacitance of greater than about 20 femtoFarads per cell.